

Radiation	Type	Technology	Case
Red	SMD	AlInGaP/AlGaAs	SMD 1206

<p>all dimensions: mm all tolerances: $\pm 0,1$</p> <p>pad 1,15 x 1,0</p> <p>cathode</p> <p>R0,3</p> <p>1,6</p> <p>1,0</p> <p>1,2</p> <p>3,2</p>	<p>Description</p> <p>High-power, high speed LED in standard SMD package, compact design allows for easy circuit board mounting and assembling of arrays</p> <p>Applications</p> <p>Illumination, indicators, measurement applications and security systems, automation</p>
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Absolute Maximum Ratings

at $T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
DC forward current		I_F	20	mA
Peak forward current	$t_p \leq 100 \mu\text{s}, t_p/T \leq 0.1$	I_{FM}	50	mA
Power dissipation		P	50	mW
Operating temperature range		T_{amb}	-20 to +85	°C
Storage temperature range		T_{stg}	-55 to +100	°C

Electrical and Optical Characteristics

at $T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		2,0	2,5	V
Reverse voltage	$I_F = 100 \mu\text{A}$	V_R	5			V
Radiant power	$I_F = 20 \text{ mA}$	Φ_e	1,1	1,4		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p	625	635	645	nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		18		nm
Viewing angle	$I_F = 20 \text{ mA}$	φ		120		deg.
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		10		ns

Note: All measurements carried out with *EPIGAP* equipment

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.

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